

REVISIONS			
LTR	DESCRIPTION	DATE (YR-MO-DA)	APPROVED
A	Update boilerplate to MIL-PRF-38535 requirements. – LTG	06-11-21	Thomas M. Hess
B	Update boilerplate paragraphs to the current MIL-PRF-38535 requirements. - LTG	13-01-25	Thomas M. Hess

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REV STATUS	REV	B	B	B	B	B	B	B	B	B	B	B	B	B	B	B	B			
OF SHEETS	SHEET	1	2	3	4	5	6	7	8	9	10	11	12	13						
PMIC N/A	PREPARED BY Marcia B. Kelleher	<p align="center">DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990 http://www.landandmaritime.dla.mil</p> <p>MICROCIRCUIT, DIGITAL, ADVANCED CMOS, DUAL 1-OF-4 DATA SELECTORS/MULTIPLEXERS WITH THREE-STATE OUTPUTS AND TTL COMPATIBLE INPUTS, MONOLITHIC SILICON</p>																		
<p align="center">STANDARD MICROCIRCUIT DRAWING</p> <p>THIS DRAWING IS AVAILABLE FOR USE BY ALL DEPARTMENTS AND AGENCIES OF THE DEPARTMENT OF DEFENSE</p> <p align="center">AMSC N/A</p>	CHECKED BY Thomas J. Riccuiti																			
	APPROVED BY Michael A. Frye																			
	DRAWING APPROVAL DATE 90-10-01																			
	REVISION LEVEL B																			
	SIZE A	CAGE CODE 67268	5962-90906																	
	SHEET		1 OF 13																	

1.3 Absolute maximum ratings. 1/ 2/ 3/

Supply voltage range (V_{CC})	-0.5 V dc to +7.0 V dc
Input voltage range (V_{IN})	-0.5 V dc to $V_{CC} + 0.5$ V dc
Output voltage range (V_{OUT})	-0.5 V dc to $V_{CC} + 0.5$ V dc
Input clamp current (I_{IK})	± 20 mA
Output clamp current (I_{OK})	± 50 mA
Continuous output current (I_{OUT})	± 50 mA
V_{CC} or GND current (I_{CC} , I_{GND})	± 100 mA
Storage temperature range (T_{STG})	-65°C to +150°C
Maximum power dissipation (P_D)	500 mW
Lead temperature (soldering 10 seconds)	+300°C
Thermal resistance, junction-to-case (θ_{JC})	See MIL-STD-1835
Junction temperature (T_J)	+175°C 4/

1.4 Recommended operating conditions. 2/ 3/

Supply voltage range (V_{CC})	+4.5 V dc to +5.5 V dc
Input voltage range (V_{IN})	0.0 V dc to V_{CC}
Output voltage range (V_{OUT})	0.0 V dc to V_{CC}
Minimum high level input voltage (V_{IH})	2.0 V
Maximum low level input voltage (V_{IL})	0.8 V
Case operating temperature range (T_C)	-55°C to +125°C
Input rise or fall time (t_r , t_f)	0 to 10 ns/V

2. APPLICABLE DOCUMENTS

2.1 Government specification, standards, and handbooks. The following specification, standards, and handbooks form a part of this drawing to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

DEPARTMENT OF DEFENSE SPECIFICATION

MIL-PRF-38535 - Integrated Circuits, Manufacturing, General Specification for.

DEPARTMENT OF DEFENSE STANDARDS

MIL-STD-883 - Test Method Standard Microcircuits.
 MIL-STD-1835 - Interface Standard Electronic Component Case Outlines.

DEPARTMENT OF DEFENSE HANDBOOKS

MIL-HDBK-103 - List of Standard Microcircuit Drawings.
 MIL-HDBK-780 - Standard Microcircuit Drawings.

(Copies of these documents are available online at <https://assist.dla.mil/quicksearch/> or from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

- 1/ Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability
- 2/ Unless otherwise specified, all voltages are referenced to GND.
- 3/ The limits for the parameters specified herein shall apply over the full specified V_{CC} range and case temperature range of -55°C to +125°C.
- 4/ Maximum junction temperature shall not be exceeded except for allowable short duration burn-in screening conditions per method 5004 of MIL-STD-883.

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2.2 Non-Government publications. The following document(s) form a part of this document to the extent specified herein. Unless otherwise specified, the issues of these documents cited in the solicitation or contract.

JEDEC – SOLID STATE TECHNOLOGY ASSOCIATION (JEDEC)

JESD20 - Standard for Description of 54/74ACXXXXX and 54/74ACTXXXXX Advanced High-Speed CMOS Devices.

(Copies of these documents are available online at <http://www.jedec.org> or from JEDEC – Solid State Technology Association, 3103 North 10th Street, Suite 240-S Arlington, VA 22201-2107).

2.3 Order of precedence. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

3.1 Item requirements. The individual item requirements for device classes Q and V shall be in accordance with MIL-PRF-38535 as specified herein, or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. The individual item requirements for device class M shall be in accordance with MIL-PRF-38535, appendix A for non-JAN class level B devices and as specified herein.

3.2 Design, construction, and physical dimensions. The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein for device classes Q and V or MIL-PRF-38535, appendix A and herein for device class M.

3.2.1 Case outlines. The case outlines shall be in accordance with 1.2.4 herein.

3.2.2 Terminal connections. The terminal connections shall be as specified on figure 1.

3.2.3 Truth table. The truth table shall be as specified on figure 2.

3.2.4 Logic diagram. The logic diagram shall be as specified on figure 3.

3.2.5 Switching waveforms and test circuit. The switching waveforms and test circuit shall be as specified on figure 4.

3.3 Electrical performance characteristics and postirradiation parameter limits. Unless otherwise specified herein, the electrical performance characteristics and postirradiation parameter limits are as specified in table I and shall apply over the full case operating temperature range.

3.4 Electrical test requirements. The electrical test requirements shall be the subgroups specified in table II. The electrical tests for each subgroup are defined in table I.

3.5 Marking. The part shall be marked with the PIN listed in 1.2 herein. In addition, the manufacturer's PIN may also be marked. For packages where marking of the entire SMD PIN number is not feasible due to space limitations, the manufacturer has the option of not marking the "5962-" on the device. For RHA product using this option, the RHA designator shall still be marked. Marking for device classes Q and V shall be in accordance with MIL-PRF-38535. Marking for device class M shall be in accordance with MIL-PRF-38535, appendix A.

3.5.1 Certification/compliance mark. The certification mark for device classes Q and V shall be a "QML" or "Q" as required in MIL-PRF-38535. The compliance mark for device class M shall be a "C" as required in MIL-PRF-38535, appendix A.

3.6 Certificate of compliance. For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see 6.6.1 herein). For device class M, a certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-HDBK-103 (see 6.6.2 herein). The certificate of compliance submitted to DLA Land and Maritime-VA prior to listing as an approved source of supply for this drawing shall affirm that the manufacturer's product meets, for device classes Q and V, the requirements of MIL-PRF-38535 and herein or for device class M, the requirements of MIL-PRF-38535, appendix A and herein.

3.7 Certificate of conformance. A certificate of conformance as required for device classes Q and V in MIL-PRF-38535 or for device class M in MIL-PRF-38535, appendix A shall be provided with each lot of microcircuits delivered to this drawing.

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3.8 Notification of change for device class M. For device class M, notification to DLA Land and Maritime-VA of change of product (see 6.2 herein) involving devices acquired to this drawing is required for any change that affects this drawing.

3.9 Verification and review for device class M. For device class M, DLA Land and Maritime, DLA Land and Maritime's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.

3.10 Microcircuit group assignment for device class M. Device class M devices covered by this drawing shall be in microcircuit group number 39 (see MIL-PRF-38535, appendix A).

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TABLE I. Electrical performance characteristics.

Test	Symbol	Test conditions -55°C ≤ T _C ≤ +125°C unless otherwise specified		Group A subgroups	Device type	Limits		Unit
						Min	Max	
High level output voltage	V _{OH}	I _{OH} = -50 μA	V _{CC} = 4.5 V	1, 2, 3	All	4.4		V
			V _{CC} = 5.5 V			5.4		
		I _{OH} = -24 mA	V _{CC} = 4.5 V			3.7		
			V _{CC} = 5.5 V			4.7		
I _{OH} = -50 mA <u>1/</u>	V _{CC} = 5.5 V	3.85						
Low level output voltage	V _{OL}	I _{OL} = 50 μA	V _{CC} = 4.5 V	1, 2, 3	All		0.1	V
			V _{CC} = 5.5 V			0.1		
		I _{OL} = 24 mA	V _{CC} = 4.5 V			0.5		
			V _{CC} = 5.5 V			0.5		
		I _{OL} = 50 mA <u>1/</u>	V _{CC} = 5.5 V			1.65		
Off-state output current, voltage applied	I _{OZ}	V _{OUT} = V _{CC} or GND	V _{CC} = 5.5 V	1, 2, 3	All		±10.0	μA
Input leakage current, low	I _{IL}	V _{IN} = 0.0 V	V _{CC} = 5.5 V	1, 2, 3	All		-1.0	μA
Input leakage current, high	I _{IH}	V _{IN} = 5.5 V	V _{CC} = 5.5 V	1, 2, 3	All		+1.0	μA
Quiescent supply current	I _{CC}	V _{IN} = V _{CC} or GND I _{OUT} = 0.0 mA	V _{CC} = 5.5 V	1, 2, 3	All		160	μA
Quiescent supply current delta <u>2/</u>	ΔI _{CC}	One input at 3.4 V Other inputs at V _{CC} or GND	V _{CC} = 5.5 V	1, 2, 3	All		1.0	mA
Input capacitance	C _{IN}	See 4.4.1c		4	All		7	pF
Output capacitance	C _{OUT}	See 4.4.1c		4	All		16	pF
Power dissipation capacitance (per multiplexer) <u>3/</u>	C _{PD}	V _{IN} = V _{CC} or GND C _L = 50 pF, f = 1 MHz Outputs enabled See 4.4.1c	V _{CC} = 5.0 V	4	All		49	pF
		V _{IN} = V _{CC} or GND C _L = 50 pF, f = 1 MHz Outputs disabled See 4.4.1c	V _{CC} = 5.0 V	4	All		24	pF
Functional tests		V _{CC} = 5.5 V See 4.4.1d		7, 8	All			

See footnotes at end of table.

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TABLE I. Electrical performance characteristics – Continued.

Test	Symbol	Test conditions -55°C ≤ T _C ≤ +125°C unless otherwise specified		Group A subgroups	Device type	Limits		Unit
						Min	Max	
Propagation delay time, from A and B to any Y	t _{PLH1}	C _L = 50 pF R _L = 500Ω See figure 4	V _{CC} = 4.5 V	9	All	1.5	11.1	ns
				10, 11		1.5	13.8	
	t _{PHL1}		V _{CC} = 4.5 V	9		1.5	8.3	
				10, 11		1.5	10.1	
Propagation delay time, from any C to any Y	t _{PLH2}	C _L = 50 pF R _L = 500Ω See figure 4	V _{CC} = 4.5 V	9	All	1.5	9.8	ns
				10, 11		1.5	12.3	
	t _{PHL2}		V _{CC} = 4.5 V	9		1.5	7.2	
				10, 11		1.5	10.5	
Propagation delay time, output enable, \bar{G} to any Y	t _{PZH}	C _L = 50 pF R _L = 500Ω See figure 4	V _{CC} = 4.5 V	9	All	1.5	6.8	ns
				10, 11		1.5	7.9	
	t _{PZL}		V _{CC} = 4.5 V	9		1.5	6.7	
				10, 11		1.5	7.8	
Propagation delay time, output disable, \bar{G} to any Y	t _{PHZ}	C _L = 50 pF R _L = 500Ω See figure 4	V _{CC} = 4.5 V	9	All	1.5	7.8	ns
				10, 11		1.5	8.6	
	t _{PLZ}		V _{CC} = 4.5 V	9		1.5	6.9	
				10, 11		1.5	7.6	

1/ Not more than one output will be tested at one time, and the duration of the test shall not exceed 10 ms.

2/ This is the increase in supply current for each input that is at one of the specified TTL voltage levels rather than 0.0 V or V_{CC}.

3/ Power dissipation capacitance (C_{PD}) determines both the dynamic power consumption (P_D) and the dynamic current consumption (I_S).

Where:

$$P_D = (C_{PD} + C_L) (V_{CC} \times V_{CC})f + (I_{CC} \times V_{CC}) + (n \times d \times \Delta I_{CC} \times V_{CC})$$

$$I_S = (C_{PD} + C_L) V_{CC}f + I_{CC} + (n \times d \times \Delta I_{CC})$$

For both P_D and I_S, n is number of device inputs at TTL levels; f is the frequency of the input signal; d is duty cycle of the input signal; and C_L is the external output load capacitance.

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Device type		01
Case outlines	E	2
Terminal number	Terminal symbol	
1	A	NC
2	B	1C3
3	1Y	1C2
4	GND	1C1
5	2Y	1C0
6	1 \bar{G}	NC
7	2 \bar{G}	A
8	2C3	B
9	2C2	1Y
10	2C1	GND
11	2C0	NC
12	V _{CC}	2Y
13	1C3	1 \bar{G}
14	1C2	2 \bar{G}
15	1C1	2C3
16	1C0	NC
17	---	2C2
18	---	2C1
19	---	2C0
20	---	V _{CC}

NC = No internal connection

FIGURE 1. Terminal connections.

Select Inputs		Data Inputs				Strobe	Output
B	A	C0	C1	C2	C3	\bar{G}	Y
X	X	X	X	X	X	H	Z
L	L	L	X	X	X	L	H
L	L	H	X	X	X	L	L
L	H	X	L	X	X	L	H
L	H	X	H	X	X	L	L
H	L	X	X	L	X	L	H
H	L	X	X	H	X	L	L
H	H	X	X	X	L	L	H
H	H	X	X	X	H	L	L

H = High voltage level
L = Low voltage level
X = Irrelevant
Z = High impedance state

FIGURE 2. Truth table.

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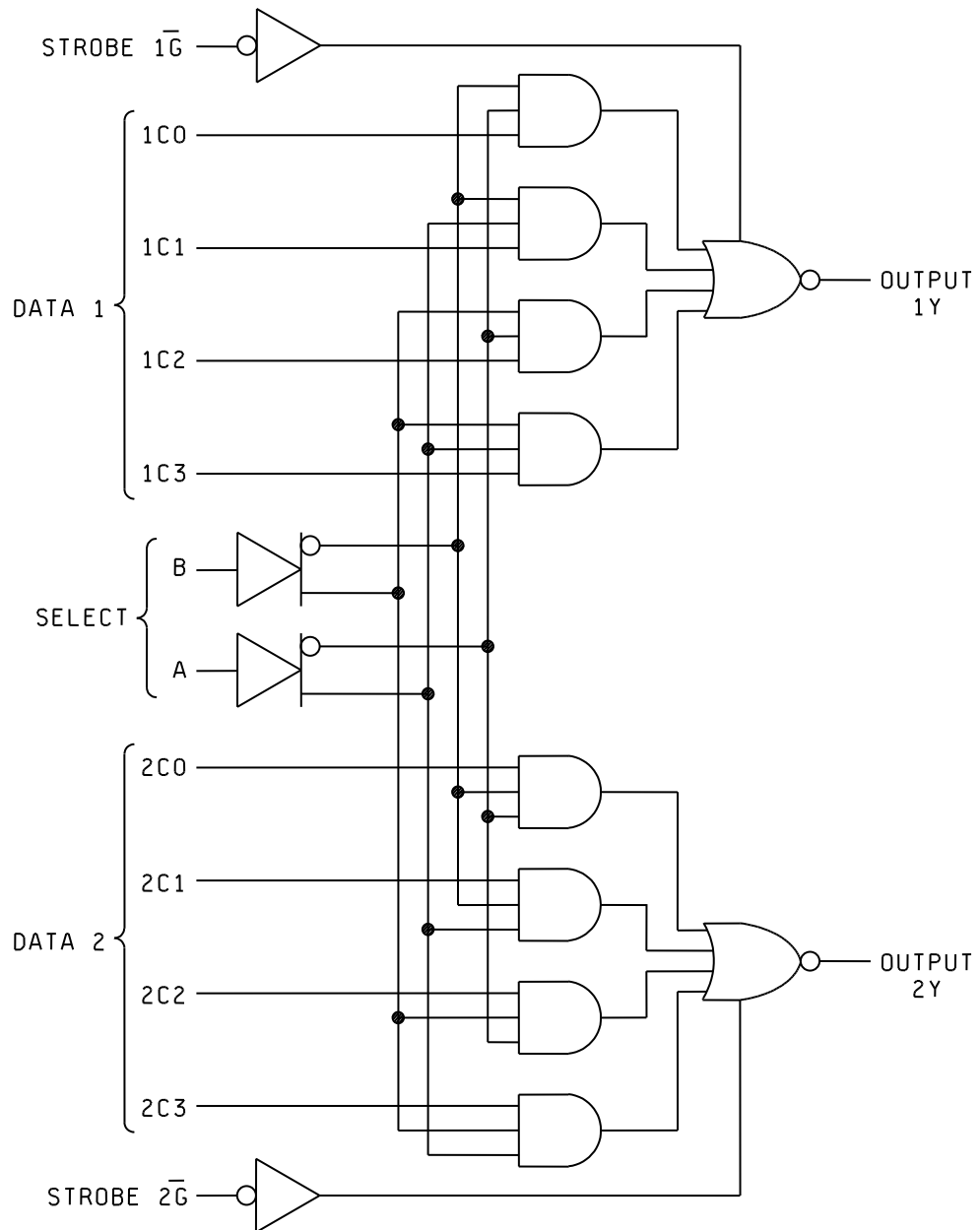


FIGURE 3. Logic diagram.

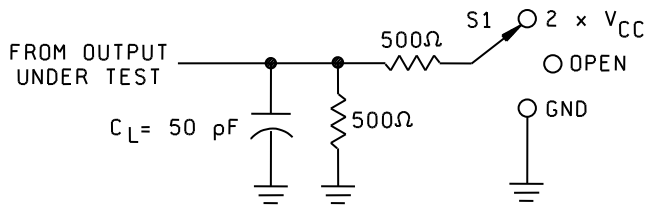
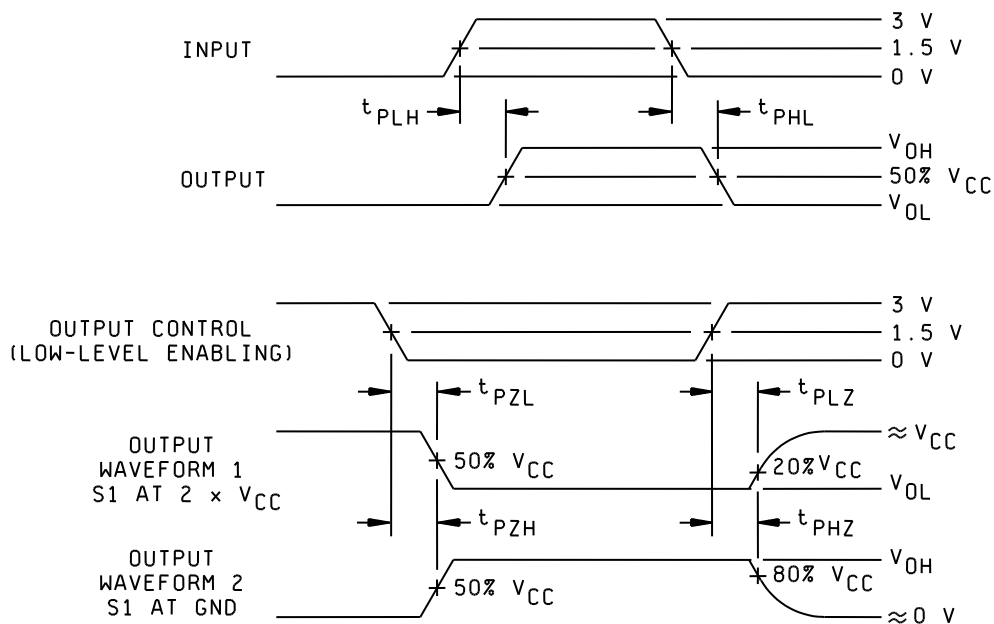
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DLA LAND AND MARITIME
COLUMBUS, OHIO 43218-3990

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TEST	S1
t_{PLH} / t_{PHL}	OPEN
t_{PLZ} / t_{PZL}	$2 \times V_{CC}$
t_{PHZ} / t_{PZH}	GND

NOTES:

1. When measuring t_{PLZ} and t_{PZL} : $V_{TEST} = 2 \times V_{CC}$.
2. When measuring t_{PHZ} , t_{PZH} : $V_{TEST} = GND$. t_{PLH} , and t_{PHL} : $V_{TEST} = \text{open}$.
3. Waveform 1 is for the output under test with internal conditions such that the output is at V_{OL} except when disabled by the output control. Waveform 2 is for the output under test with internal conditions such that the output is at V_{OH} except when disabled by the output control.
4. $C_L = 50 \text{ pF}$ minimum or equivalent (includes test jig and probe capacitance).
5. $R_L = 500\Omega$.
6. Input signal from pulse generator: $V_{IN} = 0.0 \text{ V}$ to 3.0 V ; $PRR \leq 10 \text{ MHz}$; $t_r \leq 3.0 \text{ ns}$; $t_f \leq 3.0 \text{ ns}$; t_r and t_f shall be measured from 0.3 V to 2.7 V and from 2.7 V to 0.3 V , respectively; output impedance = 50Ω ; duty cycle = 50 percent.
7. Timing parameters shall be tested at a minimum input frequency of 1 MHz.
8. The outputs are measured one at a time with one transition per measurement.

FIGURE 4. Switching waveforms and test circuit.

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4. VERIFICATION

4.1 Sampling and inspection. For device classes Q and V, sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. For device class M, sampling and inspection procedures shall be in accordance with MIL-PRF-38535, appendix A.

4.2 Screening. For device classes Q and V, screening shall be in accordance with MIL-PRF-38535, and shall be conducted on all devices prior to qualification and technology conformance inspection. For device class M, screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection.

4.2.1 Additional criteria for device class M.

- a. Burn-in test, method 1015 of MIL-STD-883.
 - (1) Test condition A, B, C, or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1015 of MIL-STD-883.
 - (2) $T_A = +125^{\circ}\text{C}$, minimum.
- b. Interim and final electrical test parameters shall be as specified in table II herein.

4.2.2 Additional criteria for device classes Q and V.

- a. The burn-in test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document revision level control of the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1015 of MIL-STD-883.
- b. Interim and final electrical test parameters shall be as specified in table II herein.
- c. Additional screening for device class V beyond the requirements of device class Q shall be as specified in MIL-PRF-38535, appendix B.

4.3 Qualification inspection for device classes Q and V. Qualification inspection for device classes Q and V shall be in accordance with MIL-PRF-38535. Inspections to be performed shall be those specified in MIL-PRF-38535 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).

4.4 Conformance inspection. Technology conformance inspection for classes Q and V shall be in accordance with MIL-PRF-38535 including groups A, B, C, D, and E inspections, and as specified herein. Quality conformance inspection for device class M shall be in accordance with MIL-PRF-38535, appendix A and as specified herein. Inspections to be performed for device class M shall be those specified in method 5005 of MIL-STD-883 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).

4.4.1 Group A inspection.

- a. Tests shall be as specified in table II herein.
- b. Subgroups 5 and 6 in table I, method 5005 of MIL-STD-883 shall be omitted.
- c. Subgroup 4 (C_{IN} , C_{OUT} , and C_{PD} measurements) shall be measured only for the initial test and after process or design changes which may affect capacitance. Test all applicable pins on 5 devices with zero failures.
- d. For device class M, subgroups 7 and 8 tests shall be sufficient to verify the truth table as specified on figure 2 herein. For device classes Q and V, subgroups 7 and 8 shall include verifying the functionality of the device.

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TABLE II. Electrical test requirements.

Test requirements	Subgroups (in accordance with MIL-STD-883, method 5005, table I)	Subgroups (in accordance with MIL-PRF-38535, table III)	
	Device class M	Device class Q	Device class V
Interim electrical parameters (see 4.2)	---	1	1
Final electrical parameters (see 4.2)	1, 2, 3, 7, 8, 9, 10, 11 <u>1/</u>	1, 2, 3, 7, 8, 9, 10, 11 <u>1/</u>	1, 2, 3, 7, 8, 9, 10, 11 <u>2/</u>
Group A test requirements (see 4.4)	1, 2, 3, 4, 7, 8, 9, 10, 11	1, 2, 3, 4, 7, 8, 9, 10, 11	1, 2, 3, 4, 7, 8, 9, 10, 11
Group C end-point electrical parameters (see 4.4)	1, 2, 3	1, 2, 3	1, 2, 3
Group D end-point electrical parameters (see 4.4)	1, 2, 3	1, 2, 3	1, 2, 3
Group E end-point electrical parameters (see 4.4)	1, 7, 9	1, 7, 9	1, 7, 9

1/ PDA applies to subgroup 1.

2/ PDA applies to subgroups 1 and 7.

4.4.2 Group C inspection. The group C inspection end-point electrical parameters shall be as specified in table II herein.

4.4.2.1 Additional criteria for device class M. Steady-state life test conditions, method 1005 of MIL-STD-883:

- a. Test condition A, B, C, or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1005 of MIL-STD-883.
- b. $T_A = +125^\circ\text{C}$, minimum.
- c. Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.

4.4.2.2 Additional criteria for device classes Q and V. The steady-state life test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The test circuit shall be maintained under document revision level control by the device manufacturer's TRB in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1005 of MIL-STD-883.

4.4.3 Group D inspection. The group D inspection end-point electrical parameters shall be as specified in table II herein.

4.4.4 Group E inspection. Group E inspection is required only for parts intended to be marked as radiation hardness assured (see 3.5 herein).

- a. End-point electrical parameters shall be as specified in table II herein.
- b. For device classes Q and V, the devices or test vehicle shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535 for the RHA level being tested. For device class M, the devices shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535, appendix A for the RHA level being tested. All device classes must meet the postirradiation end-point electrical parameter limits as defined in table I at $T_A = +25^\circ\text{C} \pm 5^\circ\text{C}$, after exposure, to the subgroups specified in table II herein.

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5. PACKAGING

5.1 Packaging requirements. The requirements for packaging shall be in accordance with MIL-PRF-38535 for device classes Q and V or MIL-PRF-38535, appendix A for device class M.

6. NOTES

6.1 Intended use. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.

6.1.1 Replaceability. Microcircuits covered by this drawing will replace the same generic device covered by a contractor prepared specification or drawing.

6.1.2 Substitutability. Device class Q devices will replace device class M devices.

6.2 Configuration control of SMD's. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished using DD Form 1692, Engineering Change Proposal.

6.3 Record of users. Military and industrial users should inform DLA Land and Maritime when a system application requires configuration control and which SMD's are applicable to that system. DLA Land and Maritime will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronic devices (FSC 5962) should contact DLA Land and Maritime-VA, telephone (614) 692-0547.

6.4 Comments. Comments on this drawing should be directed to DLA Land and Maritime-VA, Columbus, Ohio 43218-3990, or telephone (614) 692-0540.

6.5 Abbreviations, symbols, and definitions. The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535 and MIL-HDBK-1331.

6.6 Sources of supply.

6.6.1 Sources of supply for device classes Q and V. Sources of supply for device classes Q and V are listed in MIL-HDBK-103 and QML-38535. The vendors listed in QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DLA Land and Maritime-VA and have agreed to this drawing.

6.6.2 Approved sources of supply for device class M. Approved sources of supply for class M are listed in MIL-HDBK-103. The vendors listed in MIL-HDBK-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to and accepted by DLA Land and Maritime-VA.

STANDARD MICROCIRCUIT DRAWING DLA LAND AND MARITIME COLUMBUS, OHIO 43218-3990	SIZE A		5962-90906
		REVISION LEVEL B	SHEET 13

STANDARD MICROCIRCUIT DRAWING BULLETIN

DATE: 13-01-25

Approved sources of supply for SMD 5962-90906 are listed below for immediate acquisition information only and shall be added to MIL-HDBK-103 and QML-38535 during the next revision. MIL-HDBK-103 and QML-38535 will be revised to include the addition or deletion of sources. The vendors listed below have agreed to this drawing and a certificate of compliance has been submitted to and accepted by DLA Land and Maritime-VA. This information bulletin is superseded by the next dated revision of MIL-HDBK-103 and QML-38535. DLA Land and Maritime maintains an online database of all current sources of supply at <http://www.landandmaritime.dla.mil/Programs/Smcr/>.

Standard microcircuit drawing PIN <u>1/</u>	Vendor CAGE number	Vendor similar PIN <u>2/</u>
5962-9090601MEA	3V146	54ACT11353/BEA
5962-9090601M2A	3V146	54ACT11353/B2A

1/ The lead finish shown for each PIN representing a hermetic package is the most readily available from the manufacturer listed for that part. If the desired lead finish is not listed contact the vendor to determine its availability.

2/ Caution. Do not use this number for item acquisition. Items acquired to this number may not satisfy the performance requirements of this drawing.

Vendor CAGE number

3V146

Vendor name and address

Rochester Electronics Inc.
16 Malcolm Hoyt Drive
Newburyport, MA 01950

The information contained herein is disseminated for convenience only and the Government assumes no liability whatsoever for any inaccuracies in the information bulletin.